

FIG. 2(a)

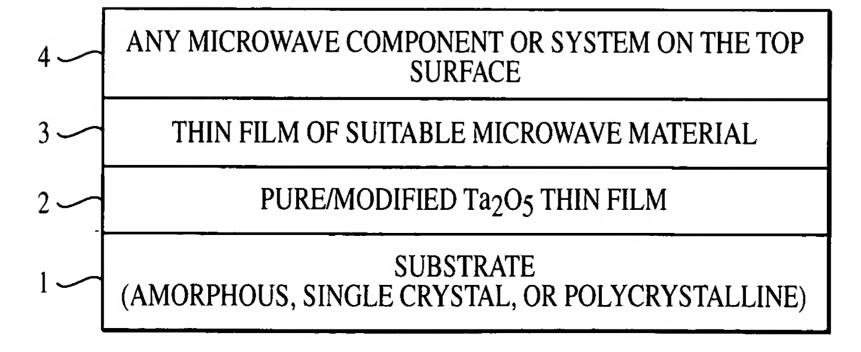
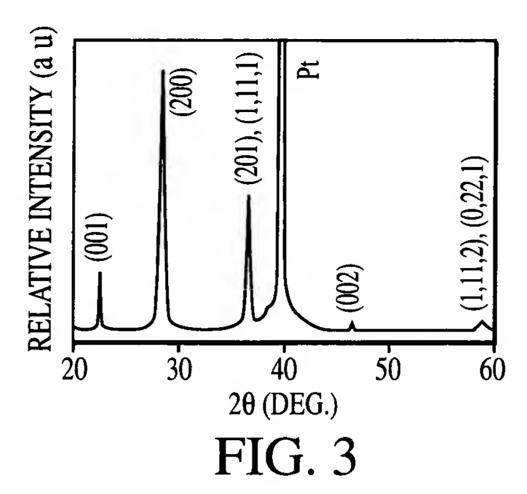
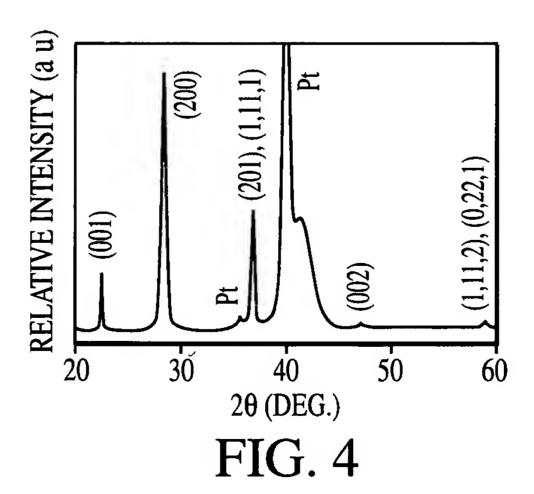


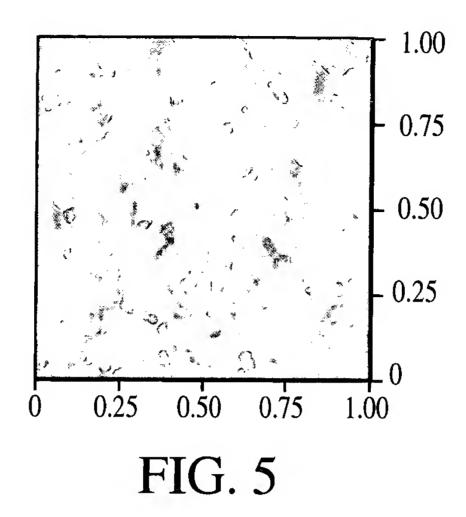
FIG. 2(b)

Fabrication of Pure and Modified Ta₂O₅ Thin Film with Enhanced Properties for Microwave Communication, Dynamic Random Access Memory and Integrated Electronic Applications, Joshi, et al. 10/661,547, CONFIRMATION NO. 9057, ARL 00-34A, Sheet 2 of 3









0.9 Ta $_2$ O $_5$ - 0.1 Al $_2$ O $_3$ THIN FILMS	
DIELECTRIC CONSTANT	42.8
DISSIPATION FACTOR	0.005
CHARGE STORAGE DENSITY	18.9 fC/μm ²
·	(AT 0.5 MV/cm)
LEAKAGE CURRENT	$<10^{-9} \text{ A/cm}^2$
DENSITY	(AT 0.5 MV/cm)
TEMPERATURE COEFFICIENT	-20 ppm/°C
OF CAPACITANCE	(RANGE 25-125 °C)
BIAS STABILITY	0.4%
OF CAPACITANCE	(UP to 1 MV/cm)
The state of the s	

FIG. 6